

IN THE CLAIMS:

Claims 3, 5, 14, 16, 24, 26, 34, 36, 46, 48, 52, 54, and 57-75 were previously cancelled. Claims 8, 12, 19, 29, 39 and 81 have been amended herein. All of the pending claims are presented below. This listing of claims will replace all prior versions and listings of claims in the application. Please enter these claims as amended.

Listing of Claims:

1. (Previously presented) A method of attaching a wafer having bumps on a surface thereof, comprising:
attaching a tape having an adhesive and a backing on to solely a portion of said bumps of said surface having bumps thereon of said wafer;
conforming at least a portion of said adhesive of said tape to said bumps, said backing of said tape has a substantially planar surface after said conforming;
providing a wafer mount having a suction surface;
applying a suction force to said backing of said tape;
removing wafer material from a back surface of said wafer while applying said suction force; and
cutting said wafer to form at least one semiconductor die after said removing wafer material from said back surface.
2. (Previously presented) The method of claim 1, removing said adhesive from said wafer prior to said cutting.
3. (Cancelled)
4. (Previously presented) The method of claim 1, wherein said applying said suction force to said backing of said tape comprises applying a suction force to said substantially planar surface of said backing.

5. (Cancelled)
6. (Original) The method of claim 1, wherein said applying a suction force to said backing of said tape includes abutting said backing to said suction surface of said wafer mount.
7. (Original) The method of claim 1, wherein said wafer comprises a wafer having a thickness of at least about 12 mils.
8. (Currently amended) The method of claim 1, wherein said removing comprises thinning said wafer to a thickness in ~~the~~ a range of between about 6 mils and about 12 mils.
9. (Previously presented) The method of claim 1, wherein said removing comprises thinning said wafer to one of about 6 mils thickness and less than about 6 mils thickness.
10. (Previously presented) The method of claim 1, wherein said removing comprises grinding said back surface of said wafer.
11. (Previously presented) The method of claim 1, wherein said removing comprises thinning said wafer by chemical-mechanical polishing said back surface of said wafer.

12. (Currently amended) A method of holding a wafer having bumps on at least a portion of a surface thereof, comprising:
applying an adhesive to solely a portion of said bumps on said surface of said wafer;
attaching a backing to at least a portion of said adhesive;
conforming at least a portion of said adhesive of said tape to said bumps, said backing of said tape has a substantially planar surface after said conforming;
providing a wafer mount having a suction surface;
holding said backing to said suction surface of said wafer mount using a suction ~~force~~ force;
removing wafer material from another surface of said wafer while holding said backing to said suction surface; and
cutting said wafer to form at least one semiconductor die after said removing wafer material from said another surface.

13. (Previously presented) The method of claim 12, further comprising:
removing said adhesive from said wafer prior to said cutting.

14. (Cancelled)

15. (Previously presented) The method of claim 12, wherein said holding said backing to said suction surface of said wafer mount comprises applying said suction force to said substantially planar surface of said backing.

16. (Cancelled)

17. (Original) The method of claim 12, wherein said holding said backing to said suction surface of said wafer mount comprises abutting at least a portion of said backing to said suction surface of said wafer mount.

18. (Original) The method of claim 12, wherein said wafer comprises a wafer having a thickness of at least about 12 mils.

19. (Currently amended) The method of claim 12, wherein said removing comprises thinning said wafer to a thickness in ~~the~~ a range of about 6 mils to about 12 mils.

20. (Previously presented) The method of claim 12, wherein said removing comprises thinning said wafer to one of a thickness of about 6 mils and a thickness of about less than 6 mils.

21. (Previously presented) The method of claim 12, wherein said removing comprises grinding said another surface of said wafer.

22. (Previously presented) The method of claim 12, wherein said removing comprises thinning said wafer by chemical-mechanical polishing said another surface of said wafer.

23. (Previously presented) A method of thinning a wafer comprising:
providing a wafer having bumps on at least a portion of a surface thereof;
attaching an adhesive having a backing to solely a portion of said bumps on said surface of said wafer;
conforming at least a portion of said adhesive of said tape to said bumps, said backing of said tape has a substantially planar surface after said conforming;
providing a wafer mount having a suction surface;
attaching said backing of said adhesive to at least a portion of said suction surface of said wafer mount using a suction force;
removing wafer material from another surface of said wafer while said backing of said adhesive attached to at least a portion of said suction surface; and
cutting said wafer to form at least one semiconductor die after said removing wafer material from said another surface.

24. (Cancelled)

25. (Previously presented) The method of claim 23, wherein said attaching said backing to at least a portion of said suction surface of said wafer mount comprises applying said suction force to said substantially planar surface of said backing.

26. (Cancelled)

27. (Previously presented) The method of claim 23, wherein said attaching said backing to at least a portion of said suction surface of said wafer mount comprises abutting at least a portion of said backing to said at least a portion of said suction surface and wherein said suction force attaches said wafer to said wafer mount.

28. (Original) The method of claim 23, wherein said wafer comprises a wafer having a thickness of at least about 12 mils.

29. (Currently amended) The method of claim 23, wherein said removing comprises thinning said wafer to a thickness in ~~the~~ a range of between about 6 mils and about 12 mils.

30. (Original) The method of claim 23, wherein said removing comprises thinning said wafer to one of about 6 mils and less than about 6 mils.

31. (Previously presented) The method of claim 23, wherein said removing comprises grinding said another surface of said wafer.

32. (Previously presented) The method of claim 23, wherein said removing comprises thinning said wafer by chemical-mechanical polishing said another surface of said wafer.

33. (Previously presented) A method of fabricating a wafer having a front surface having bumps thereon and a back surface, comprising:
applying an adhesive having a backing onto solely a portion of said bumps;
conforming at least a portion of said adhesive of said tape to said bumps, said backing of said tape has a substantially planar surface after said conforming;
providing a wafer mount having a suction surface;
attaching at least a portion of said backing to at least a portion of said suction surface of said wafer mount using a suction force;
removing wafer material from said back surface of said wafer while said at least a portion of said backing attached to at least a portion of said suction surface; and
cutting said wafer to form at least one semiconductor die after said removing wafer material from said back surface.

34. (Cancelled)

35. (Previously presented) The method of claim 33, wherein said attaching at least a portion of said backing to at least a portion of said suction surface of said wafer mount comprises applying said suction force to at least a portion of said substantially planar surface of said backing.

36. (Cancelled)

37. (Previously presented) The method of claim 33, wherein said attaching at least a portion of said backing to at least a portion of said suction surface of said wafer mount comprises abutting at least a portion of said backing to said suction surface and wherein said suction force to attach said wafer to said wafer mount.

38. (Original) The method of claim 33, wherein said wafer comprises a wafer having a thickness of at least about 12 mils.

39. (Currently amended) The method of claim 33, wherein said removing comprises thinning said wafer to a thickness in ~~the~~ a range of between about 6 mils and about 12 mils.

40. (Original) The method of claim 33, wherein said removing comprises thinning said wafer to a thickness of one of about 6 mils and less than about 6 mils.

41. (Previously presented) The method of claim 33, wherein said removing comprises grinding said back surface of said wafer.

42. (Previously presented) The method of claim 33, wherein said removing comprises thinning said wafer by chemical-mechanical polishing said back surface of said wafer.

43. (Original) The method of claim 33, further comprising:
removing said adhesive from said wafer.

44. (Previously presented) The method of claim 43, wherein said cutting said wafer comprises forming a plurality of semiconductor dies.

45. (Previously presented) A method of mounting a bumped wafer having bumps on at least a portion of a surface thereof to a wafer mounting chuck, comprising:
applying an adhesive having a backing to solely a portion of said bumps;
conforming at least a portion of said adhesive of said tape to said bumps, said backing of said tape has a substantially planar surface after said conforming;
mounting said wafer to said wafer mounting chuck using a suction force communicated through said wafer mounting chuck;
removing wafer material from a back surface of said wafer while said wafer mounted to said wafer mounting chuck; and
cutting said wafer to form at least one semiconductor die after said removing wafer material from said back surface.

46. (Cancelled)

47. (Previously presented) The method of claim 45, wherein said mounting said wafer to said wafer mounting chuck comprises applying said suction force to at least a portion of said substantially planar surface.

48. (Cancelled)

49. (Previously presented) The method of claim 45, wherein said mounting said wafer to said wafer mounting chuck comprises abutting at least a portion of said backing to a suction surface of said wafer mounting chuck.

50. (Previously presented) The method of claim 45, wherein said wafer comprises a wafer having a thickness of at least about 12 mils.

51. (Previously presented) A method of using a vacuum to hold a bumped wafer having a front surface having bumps thereon and a back surface, comprising:
applying an adhesive having a backing to solely a portion of said front surface of said wafer
covering a portion of at least one bump of said bumps thereon;
conforming at least a portion of said adhesive of said tape to said bumps, said backing of said tape has a substantially planar surface after said conforming;
holding at least a portion of said front surface of said wafer using a vacuum applied through at least a portion of a surface of a wafer mount;
removing wafer material from a back surface of said wafer while holding said at least a portion of said first surface of said wafer using said vacuum; and
cutting said wafer to form at least one semiconductor die after said removing wafer material from said back surface.

52. (Cancelled)

53. (Previously presented) The method of claim 51, wherein said holding comprises applying said vacuum to said substantially planar surface of said backing.

54. (Cancelled)

55. (Previously presented) The method of claim 51, wherein said holding comprises abutting at least a portion of said backing to said surface of the wafer mount and wherein said vacuum holds said wafer to said wafer mount.

56. (Original) The method of claim 51, wherein said wafer comprises a wafer having a thickness of at least about 12 mils.

57.-75. (Cancelled)

76. (Previously presented) A method of attaching a wafer having bumps on a surface thereof, comprising:
attaching a tape having an adhesive and a backing on at least a portion of said surface having bumps thereon of said wafer, said tape contacting about 10% to about 60% of the surface area of said bumps;
conforming at least a portion of said adhesive of said tape to said bumps, said backing of said tape having a substantially planar surface after said conforming;
providing a wafer mount having a suction surface;
applying a suction force to said backing of said tape;
removing wafer material from a back surface of said wafer while applying said suction force; and
cutting said wafer to form a plurality of semiconductor dies after removing said wafer material from said back surface.

77. (Previously presented) The method of claim 76, further comprising:
removing said adhesive from said wafer prior to said cutting.

78. (Previously presented) The method of claim 76, wherein said applying said suction force to said backing of said tape comprises applying a suction force to said substantially planar surface of said backing.

79. (Previously presented) The method of claim 76, wherein said applying a suction force to said backing of said tape includes abutting said backing to said suction surface of said wafer mount.

80. (Previously presented) The method of claim 76, wherein said wafer comprises a wafer having a thickness of at least about 12 mils.

81. (Currently amended) The method of claim 77, wherein said removing comprises thinning said wafer to a thickness in ~~the~~ a range of between about 6 mils and about 12 mils.

82. (Previously presented) The method of claim 77, wherein said removing comprises thinning said wafer to one of about 6 mils thickness and less than about 6 mils thickness.

83. (Previously presented) The method of claim 77, wherein said removing comprises grinding said back surface of said wafer.

84. (Previously presented) The method of claim 77, wherein said removing comprises thinning said wafer by chemical-mechanical polishing said back surface of said wafer.